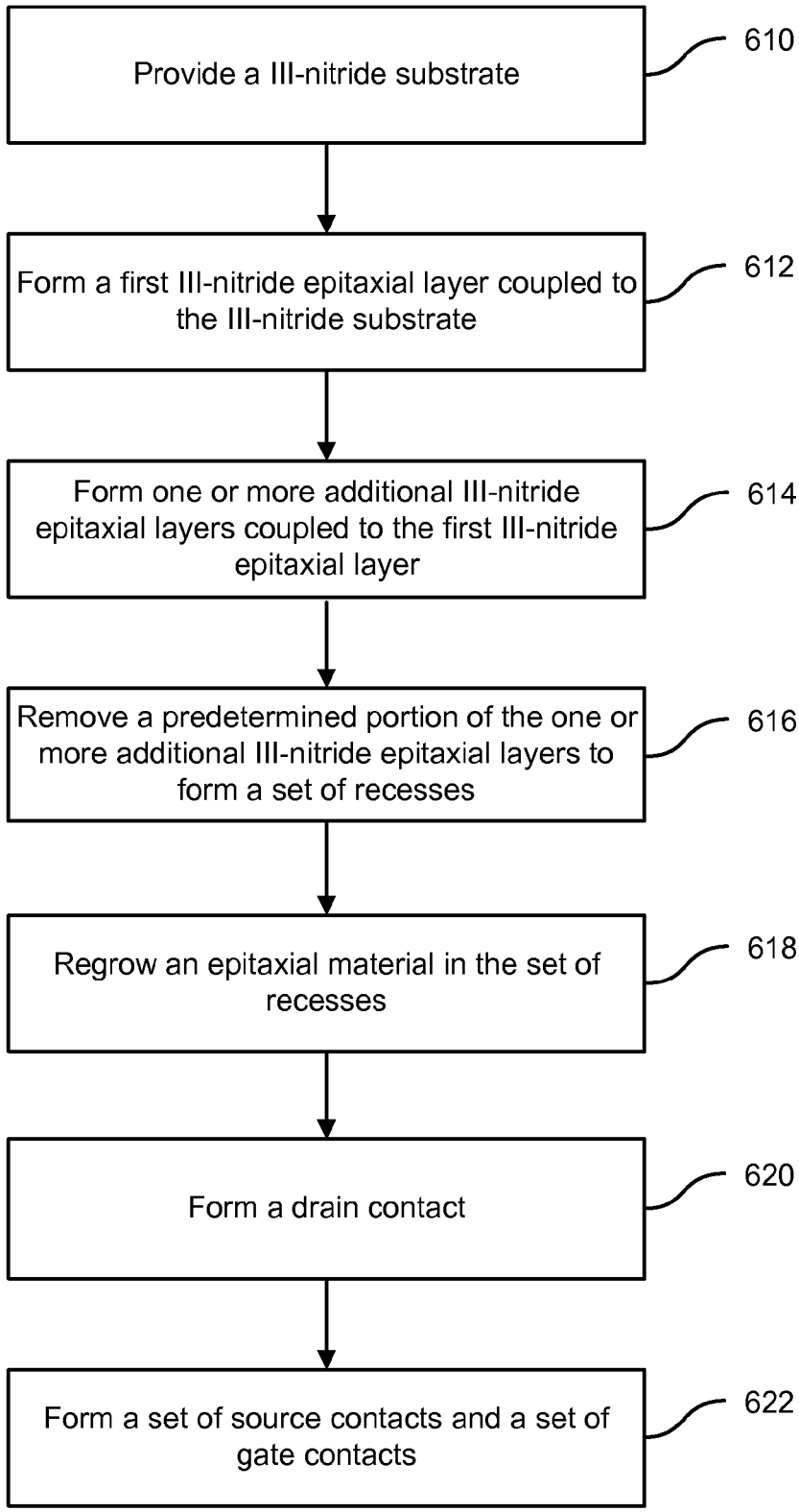
Provide a III-nitride substrate
610
Form a first III-nitride epitaxial layer coupled to the III-nitride substrate
612
Form one or more additional III-nitride epitaxial layers coupled to the first III-nitride epitaxial layer
614
Remove a predetermined portion of the one or more additional III-nitride epitaxial layers to form a set of recesses
616
Regrow an epitaxial material in the set of recesses
618
Form a drain contact
620
Form a set of source contacts and a set of gate contacts
622

FIG. 6